

Silicon Photodiode, Filter Combination Photovoltaic

FEATURES

• Large active area

PHOTONIC

- High transmission
- Low noise

DESCRIPTION

The **PDV-V400** is a silicon, PIN planar diffused, photodiode with a photopic response filter. The detector filter combination has a wide bandwidth designed to simulate the spectral response of the human eye. Packaged in a TO-5 metal can.

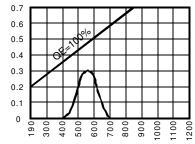
APPLICATIONS

- Photometry
- Radiometry
- Film color processing

Packaged in a TO-5 metal can. ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-20	+85	S
То	Operating Temperature Range	-15	+70	S
Ts	Soldering Temperature*		+240	с
Ι	Light Current		0.5	mA

SPECTRALRESPONSE



WAVELENGTH(nm)

RESPONSIVITY (A/W)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS			
lsc	Short Circuit Current***	H = 100 fc, 2850 K	150	200		μA			
ΙD	Dark Current	H = 0, V _R = 10 mV		10	50	pА			
Rsh	Shunt Resistance	H = 0, V _R = 10 mV	.20	2		GΩ			
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C			
CJ	Junction Capacitance	$H = 0, V_R = 10 V^{**}$		1700		pF			
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		525		nm			
HBW	Half Bandwidth	(FWHM)		150		nm			
VBR	Breakdown Voltage	I = 10 µµA	50	75		V			
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		9x10 ⁻¹⁵		W/ V Hz			
tr	Response Time	$RL = 1 K\Omega V_R = 10 V$		1.0		μS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f=1 MHz, *** without filter [FORMNO.100-PDV-V400 REVC]